

<b>L Number</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Time stamp</b>
<b>1</b>	<b>13</b>	(drift).clm. and trench.clm. and (deplete r depleted or depletion or depleting).clm. and (resistiv r resistivity or r sistance).clm.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:30
<b>2</b>	<b>9</b>	((trench near5 drift) and ((high or highly or low or lower or higher) near (resistive or resistivity)).clm. and (epitaxy or epitaxial or epitaxially).clm.) and (deplete or depleting or depleted or depletion)) and (impurity or doping or concentration).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:30
<b>3</b>	<b>8</b>	(substrate and drift and (epitaxy or epitaxial) and trench and gate and source and drain and (deplete or depletion or depleting or depleted)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:30
<b>4</b>	<b>23</b>	(((((breakdown or break-down) and (epitaxy or epitaxial or epitaxially) and (trench)) and (power and semiconductor)) and (epitaxy or epitaxial or epitaxially).ti,ab,clm.) and (breakdown or break-down).ti,ab,clm.) and trench.ti,ab,clm.) and (source and drain).ti,ab,clm.) and drift.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:31
<b>5</b>	<b>11</b>	(((((vertical near5 (mos or mosfet or fet) near5 gate near5 trench)) and drift) and (epitaxy or epitaxial)) and source and drain and (insulating or insulator or dielectric)) and (epitaxy or epitaxial).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:31
<b>6</b>	<b>69</b>	((vertical near5 (mos or mosfet or fet) near5 gate near5 trench)) and drift) and (epitaxy or epitaxial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:31
<b>7</b>	<b>31</b>	(((((vertical near5 (mos or mosfet or fet) near5 gate near5 trench)) and drift) and (epitaxy or epitaxial)) and source and drain and (insulating or insulator or dielectric)) and (drift).ti,ab,clm.) and ((width or wide or thickness or thick or concentration or impurity or doping or doped or dopant) near10 (epitaxy or epitaxial))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:31
<b>8</b>	<b>44</b>	((resistive or resistivity) near5 (semiconductor or substrate)).clm.) and drift.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:32

9	74	((((breakdown r break-down) and (epitaxy r epitaxial or epitaxially) and (tr n h)) and (p wer and semicondu tor)) and ( pitaxy r pitaxial or epitaxially).ti,ab, clm.) and (br akdown or break-d wn).ti,ab,clm.) and trench.ti,ab,clm.) and (sour e and drain).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:32
10	62	(((vertical near5 (mos or mosfet or fet) near5 gate near5 trench)) and drift) and (epitaxy or epitaxial)) and source and drain and (insulating or insulator or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:32
11	13	((epitaxial or epitaxy) near10 (deplete or depleting or depleted or depletion)) and (substrate same drift same (epitaxy or epitaxial) same trench same gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:32
12	3	(((trench near5 drift) and ((high or highly or low or lower or higher) near (resistive or resistivity)).clm. and (epitaxy or epitaxial or epitaxially).clm.) and (deplete or depleting or depleted or depletion)) and (impurity or doping or concentration).clm.) and (source and drain or electrode and base and gate).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:32
13	135	((resistive or resistivity or resistance) same (epitaxy or epitaxial or epitaxially) same drift) and ((trench) same (epitaxy or epitaxial or epitaxially) same drift)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:33
14	136	((((breakdown or break-down) and (epitaxy or epitaxial or epitaxially) and (trench)) and (power and semiconductor)) and (epitaxy or epitaxial or epitaxially).ti,ab,clm.) and (breakdown or break-down).ti,ab,clm.) and trench.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:33
15	17	(power near10 mosfet near10 gate near10 trench near10 vertical).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:34
16	6	(((power near10 mosfet near10 gate near10 trench near10 vertical) and (epitaxy or epitaxial)) and drift) and (resistive or resistor or resistivity)) and base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:34
17	2	"10091423"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/08 17:34

<b>18</b>	<b>1</b>	<b>"10/091423"</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/02/08 17:34</b>
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